

C-MOS Inverter

Last updated 12/23/23

C-MOS Inverter

- MOSFET Digital Configuration – body connections

- P-MOS body tied to V_{DD}

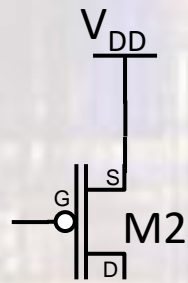


- N-MOS body tied to Gnd



C-MOS Inverter

- MOSFET Digital Configuration
 - Nominal source connections



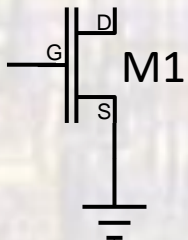
P-Channel

V_G low:

M2 is ON \rightarrow M2-drain = V_{DD}

V_G high:

M2 is OFF \rightarrow M2-drain = open



N-Channel

V_G low:

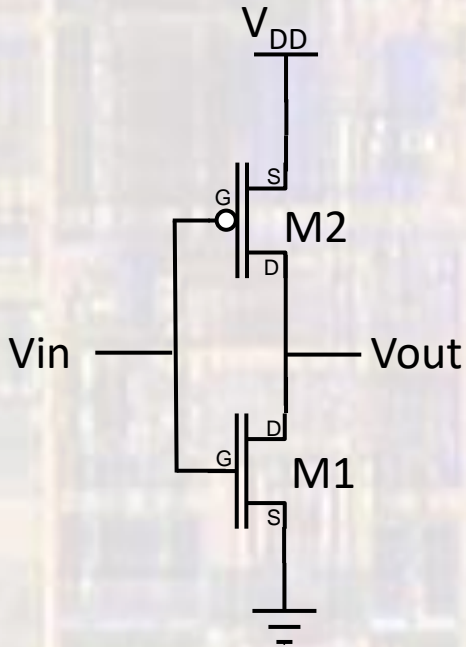
M1 is OFF \rightarrow M1-drain = open

V_G high:

M1 is ON \rightarrow M1-drain = Gnd

C-MOS Inverter

- MOSFET Digital Configuration - Inverter



Vin low:

M1 is off \rightarrow M1_D = open

M2 is on \rightarrow M2_D = V_{DD}

Vout = V_{DD}

Vin high:

M2 is on \rightarrow M2_D = open

M1 is off \rightarrow M1_D = Gnd

Vout = Gnd

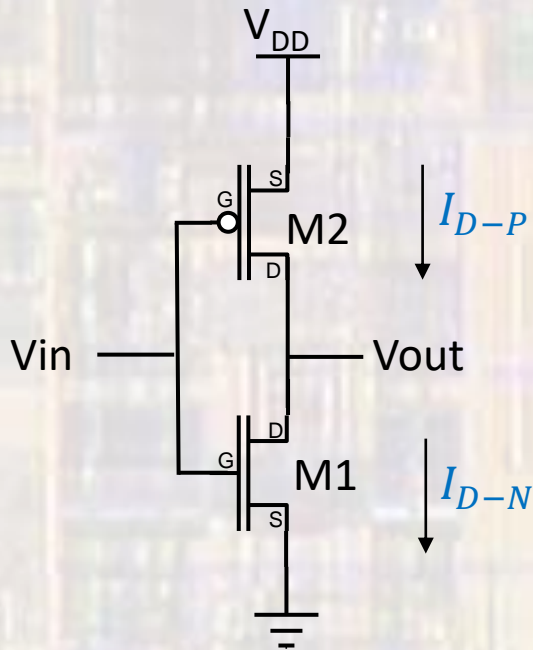
Truth Table

IN	OUT
0	1
1	0

C-MOS Inverter

- Inverter – Qualitative – DC

- Assume $V_{Tn} = V_{Tp}$, and $V_{DD} \gg V_T$



Vin low:

$V_{GS-M1} = 0 \rightarrow$ M1 Cutoff $\rightarrow I_{DS-M1} = 0 \rightarrow$ M1 is off

$V_{SG-M2} = V_{DD} (> V_{tp}) \rightarrow$ Linear or Saturated

M1 off $\rightarrow I_{DS-M1} = 0 \rightarrow I_{SD-M2} = 0 \rightarrow$ M2 Linear
 $\rightarrow V_{SD-M2} = 0$

Vout = V_{DD}

Confirm M2 Linear
 $V_{SD} < V_{SDsat} = V_{SG} - V_{Tp}$

Vin high:

$V_{SG-M2} = 0 \rightarrow$ M2 Cutoff $\rightarrow I_{SD-M2} = 0 \rightarrow$ M2 is off

$V_{GS-M1} = V_{DD} (> V_{tn}) \rightarrow$ Linear or Saturated

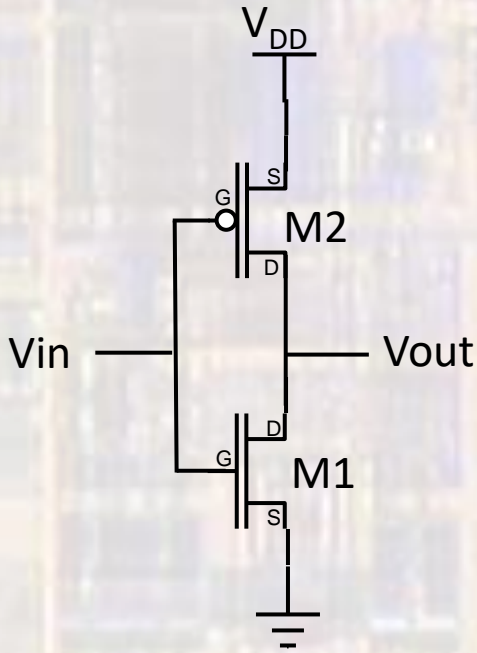
M2 off $\rightarrow I_{SD-M2} = 0 \rightarrow I_{DS-M1} = 0 \rightarrow$ M1 Linear
 $\rightarrow V_{DS-M1} = 0$

Vout = Gnd

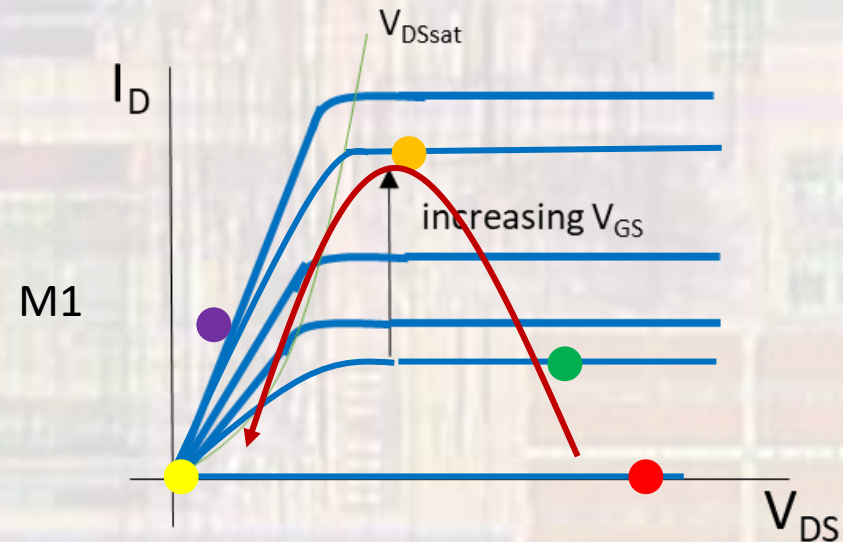
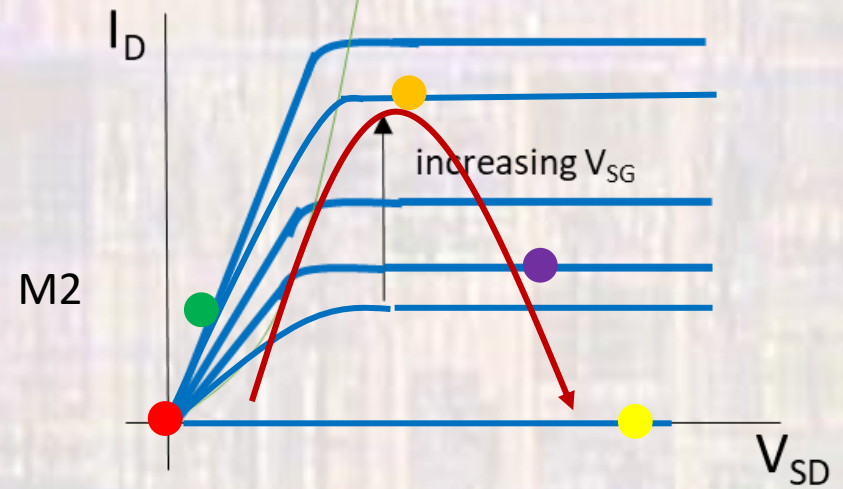
Confirm M1 Linear
 $V_{DS} < V_{DSsat} = V_{GS} - V_{Tn}$

C-MOS Inverter

- Inverter – Qualitative – DC Transfer Characteristics

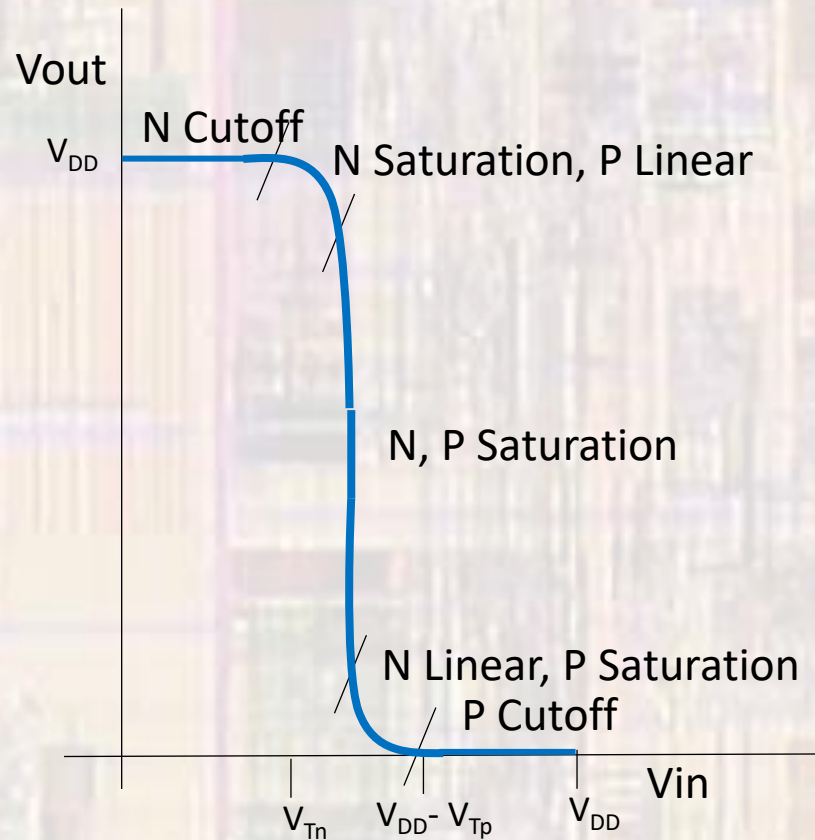
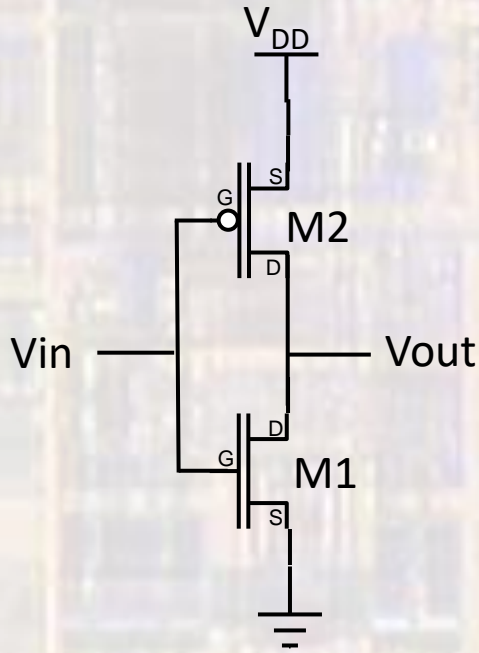


- $V_{in} < V_{Tn}$ ●
- $V_{in} > V_{Tn}, < V_{DD} - V_{Tp}, V_{out} > V_{DD}/2$ ●
- $V_{in} > V_{Tn}, < V_{DD} - V_{Tp}, V_{out} = V_{DD}/2$ ●
- $V_{in} > V_{Tn}, < V_{DD} - V_{Tp}, V_{out} < V_{DD}/2$ ●
- $V_{in} > V_{DD} - V_{Tp}$ ●



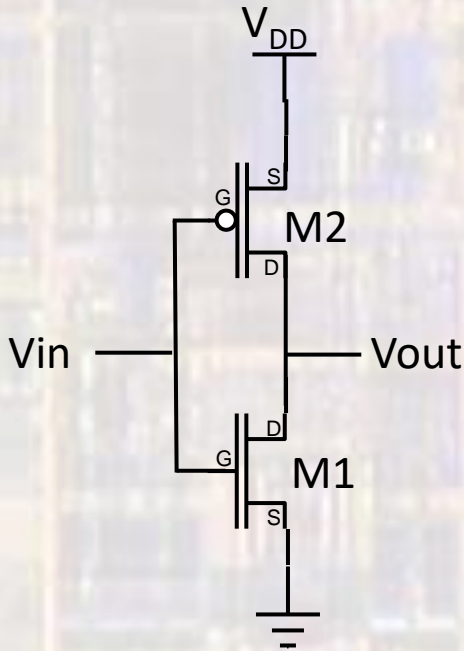
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- Inverter – Qualitative – DC Transfer Characteristics



C-MOS Inverter

- Inverter - Design



Assuming V_{dd} is big enough to keep M2 and M1 in saturation at the switching point: $I_{D-M1} = I_{D-M2}$

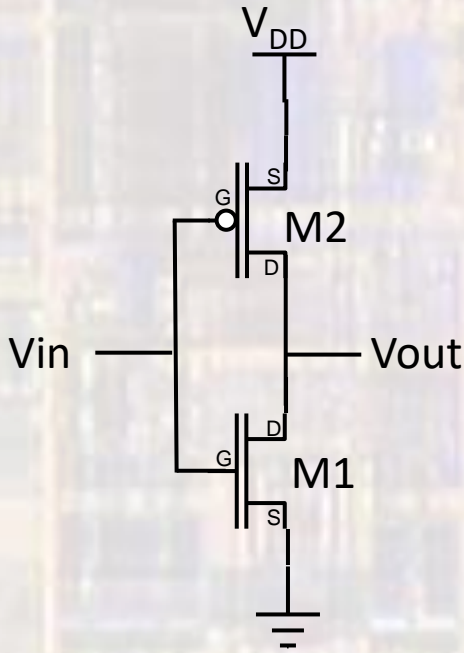
$$\frac{k'_p}{2} \frac{W2}{L2} (V_{sg2} - V_{tp})^2 = \frac{k'_n}{2} \frac{W1}{L1} (V_{gs1} - V_{tn})^2$$

Desire a consistent switching point: $V_{in} = V_{out} = V_{dd}/2$

$$\frac{k'_p}{2} \frac{W2}{L2} (V_{dd}/2 - V_{tp})^2 = \frac{k'_n}{2} \frac{W1}{L1} (V_{dd}/2 - V_{tn})^2$$

C-MOS Inverter

- Inverter – Design – cont'd



Manipulating the equation

$$\frac{W1/L1}{W2/L2} = \frac{k'_p}{k'_n} \left(\frac{V_{dd}/2 - V_{tp}}{V_{dd}/2 - V_{tn}} \right)^2$$

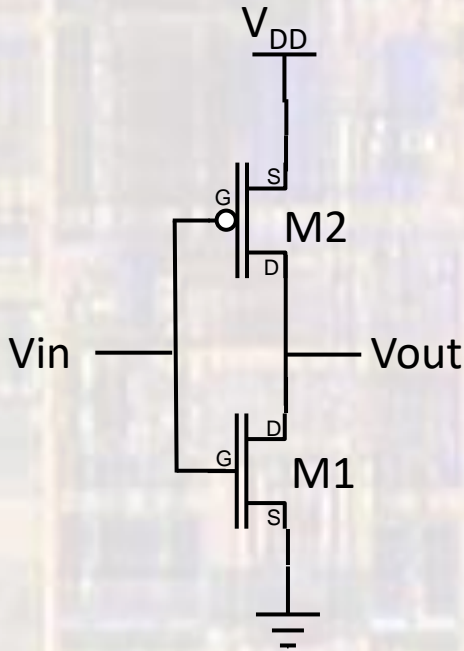
If we make $V_{tp} = V_{tn}$, V_{dd} drops out of the equation

$$\frac{W1/L1}{W2/L2} = \frac{k'_p}{k'_n}$$

And the switching point remains $V_{dd}/2$ regardless of V_{dd}

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- Inverter – Design – cont'd



Earlier we saw $k'_n = \sim 3 \times k'_p$

In a typical CMOS digital technology $L_p = L_n$

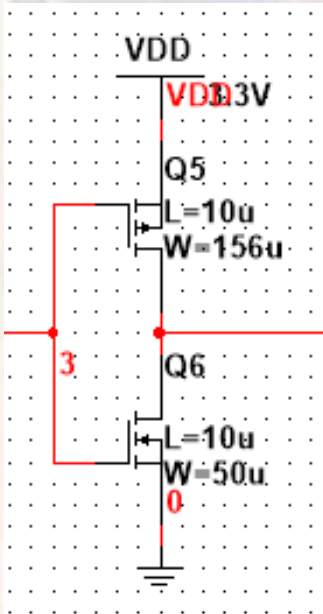
$$\frac{W_1/L_1}{W_2/L_2} = \frac{W_N/L_N}{W_P/L_P} = \frac{k'_p}{k'_n}$$

Resulting in $W_p = \sim 3 \times W_N$

With $L_p = L_n$, and $W_p = 3 \times W_N$ the current drive of the N and P are the same \rightarrow switching point = $V_{DD}/2 \rightarrow$
design is consistent with rising and falling inputs

C-MOS Inverter

- Inverter - Design



$V_{tn} = 1V$
 $V_{tp} = 1V$
 $k'n = 14\mu A/V^2$
 $k'p = 4.5\mu A/V^2$

In this case the ratio is 14/4.5 instead of 3

The circuit switches at $V_{DD}/2$ regardless of the supply voltage

